

SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

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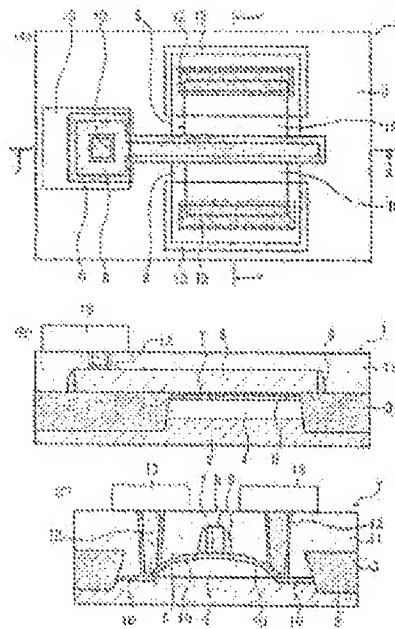
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Abstract of JP 2005101234 (A)

PROBLEM TO BE SOLVED: To provide a semiconductor device having a transistor structure of large carrier mobility and a low parasitic capacity, and having low power consumption at a high speed. ;
SOLUTION: A thin-film Si layer 5 with a source-drain 10 formed thereon is curved toward a region on source-drain 10 sides from a region extremely under a gate electrode 8. Accordingly, strain is generated in a channel region extremely under the gate electrode 8 held by the source-drain 10 in the Si layer 5, and the carrier mobility is improved. Parasitic capacitance caused by pn junction is reduced by following 4 a section under the curved Si layer 5. ;
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